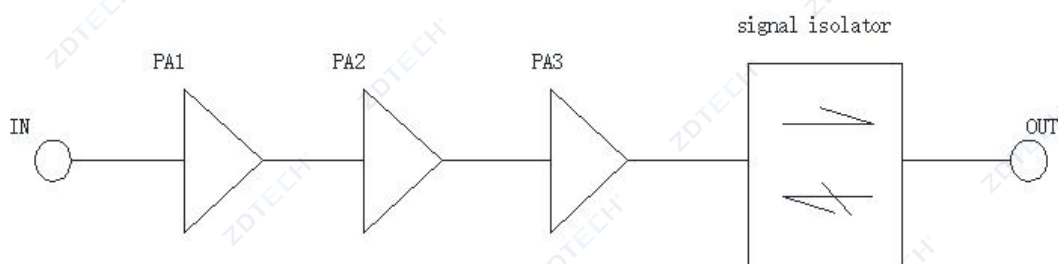


100W 0.4-6GHz GaN High Power Amplifier

Features

GaN HEMT Device
 High power
 High efficiency
 CW output
 Direct current supply
 0.4-0.75G,0.75-1.3G,1.3-2G, 2-3G、 3-4G、 4-5G, 5-5.5G, 5.5-6G

Schematic diagram



Specifications

Frequency Range	0.4-0.75G/0.75-1.3G/1.3-2G/2-3G/3-4G/4-5G/5-5.5G/5.5-6G
Output Power	50dBm
Working Mode	CW
Spurious Level	50dBc
Input Power	0±1dBm
Efficiency	>25%
Flatness Output	1dB
Input/Output VSWR	1.5:1(400-700MHz,750-1300MHz only Input)
Output Connector	N-KFD50
Temp Range	-30℃~+55℃
Supply	+28V

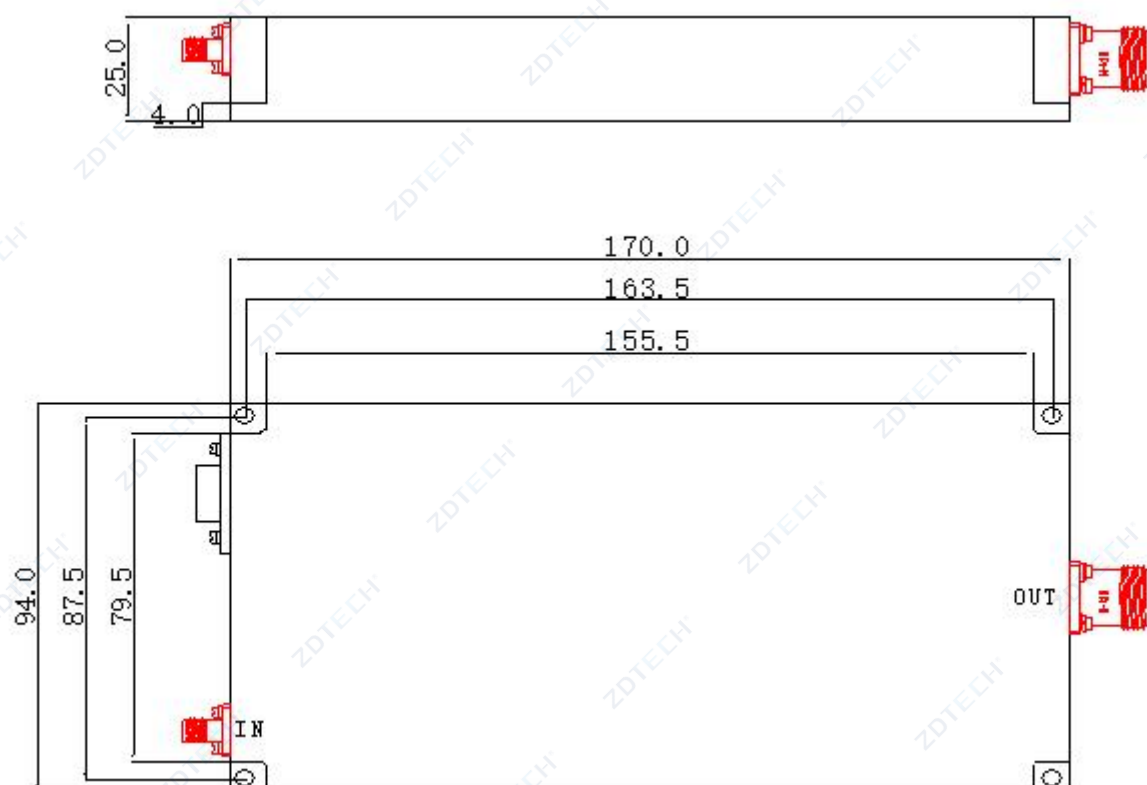
The product needs to be installed on a cold plate for contact heat dissipation.

Connector Definition

A1:+28V
 1:NC
 2:NC
 3:NC
 4:Enable:TTL,Turn on at high level
 5:Bit:Normal operation at high level
 A2:GND

Outline

100W 0.4-0.75GHz、0.75-1.3GHz、1.3-2GHz(Output without isolator)



100W 2-3G、3-4G、4-5G、5-5.5G、5.5-6G(The output has an isolator)

